om 1449A/PTO **DRMATION DISCLOSURE** MENT BY APPLICANT

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| Application Number | 10/091,373 |
| Filing Date | March 4, 2002 |
| First Named Inventor | Hiroshi ITO |
| Art Unit | 1752 |
| Examiner Name | Unassigned M. Walke |
| Attorney Docket Number | ARC920010125US1 |

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| Examiner Initials* | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), Title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where and line at the country where a line at the country where are the country where a line at | T |
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Examiner Date Signature Considered *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO

INFORMATION DESCLOSURI STATEMENT BY ARRLICANT (use as many sheets as necessary)

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Complete if Known 10/091,373 **Application Number** Filing Date March 4, 2002 First Named Inventor Hiroshi ITO Art Unit 1752 Unassigned A. Would ARC920010125US1 **Examiner Name** Attorney Docket Number

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